

Takaaki Mano

List of Publications by Year in descending order

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226
papers

4,210
citations

117625

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227
times ranked

2253
citing authors

#	ARTICLE	IF	CITATIONS
1	Improvement of structural quality of AlN layers grown on c-plane sapphire substrate by metal-organic vapor phase epitaxy using post-growth annealing with trimethylgallium. AIP Advances, 2022, 12, 015203.	1.3	0
2	Atomic-scale characterization of highly doped Si impurities in GaAs using scanning tunneling microscopy. Applied Surface Science, 2022, 583, 152373.	6.1	0
3	Real-time and space visualization of excitations of the $\nu = 1$ fractional quantum Hall edge. Physical Review Research, 2022, 4, .	3.8	1
4	Improved power and far-field pattern of surface-emitting quantum cascade lasers with strain compensation to operate at $4.3 \mu\text{m}$. Japanese Journal of Applied Physics, 2022, 61, 052001.	1.5	2
5	Anisotropic expansion of drifting spin helices in GaAs quantum wells. Physical Review B, 2021, 103, .	3.2	6
6	Polarization Anisotropies in Strain-Free, Asymmetric, and Symmetric Quantum Dots Grown by Droplet Epitaxy. Nanomaterials, 2021, 11, 443.	4.1	5
7	Annealing-Induced Structural Evolution of InAs Quantum Dots on InP (111)A Formed by Droplet Epitaxy. Crystal Growth and Design, 2021, 21, 3947-3953.	3.0	3
8	Eigenmode symmetry assignment of triangular-lattice photonic crystal slabs and their Dirac cones materialized by effective degeneracy in the mid-infrared region. Optics Express, 2021, 29, 19486.	3.4	6
9	Design and fabrication of photonic crystal resonators for single-mode and vertical surface emission from strain-compensated quantum cascade lasers operating at $4.32 \mu\text{m}$. Applied Physics Express, 2021, 14, 102003.	2.4	7
10	Patchwork metasurface quantum well photodetectors with broadened photoresponse. Optics Express, 2021, 29, 59.	3.4	5
11	Mid-IR surface-emitting Quantum Cascade Laser with Photonic Crystal. , 2021, , .		0
12	Breaking the interband detectivity limit with metasurface multi-quantum-well infrared photodetectors. Optics Express, 2021, 29, 43598.	3.4	2
13	Exciton Dynamics in Droplet Epitaxial Quantum Dots Grown on (311)A-Oriented Substrates. Nanomaterials, 2020, 10, 1833.	4.1	4
14	Effectiveness of AlGaAs barrier layers as a redistribution channel of photoexcited carriers on anomalous temperature dependence of photoluminescence properties of GaAs quantum dots. Journal of Applied Physics, 2020, 128, 055701.	2.5	2
15	Strain relaxation in InAs heteroepitaxy on lattice-mismatched substrates. Scientific Reports, 2020, 10, 4606.	3.3	27
16	Synchronously wired infrared antennas for resonant single-quantum-well photodetection up to room temperature. Nature Communications, 2020, 11, 565.	12.8	40
17	Single photon emission from droplet epitaxial quantum dots in the standard telecom window around a wavelength of $1.55 \mu\text{m}$. Applied Physics Express, 2020, 13, 025002.	2.4	20
18	Direct observation of charge accumulation in quantum well solar cells by cross-sectional Kelvin probe force microscopy. Applied Physics Letters, 2020, 116, .	3.3	2

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19	Spin-locked transport in a two-dimensional electron gas. <i>Physical Review B</i> , 2020, 101, .	3.2	5
20	Mid-IR Dirac-cone dispersion relation materialized in SOI photonic crystal slabs. <i>Optics Express</i> , 2020, 28, 4194.	3.4	9
21	Angle-resolved reflection spectra of Dirac cones in triangular-lattice photonic crystal slabs. <i>Optics Express</i> , 2020, 28, 21601.	3.4	7
22	Systematic studies for improving device performance of quantum well infrared stripe photodetectors. <i>Nanophotonics</i> , 2020, 9, 3373-3384.	6.0	10
23	Near-field resonant photon sorting applied: dual-band metasurface quantum well infrared photodetectors for gas sensing. <i>Nanophotonics</i> , 2020, 9, 4775-4784.	6.0	13
24	Surface-emitting Quantum Cascade Laser with Photonic Crystal at $4\frac{1}{4}\mu\text{m}$. , 2020, , .		0
25	Metasurface Quantum Well Photodetectors with Broadened Photoresponse Using a Patchwork of Cavities within a Subwavelength Period. , 2020, , .		1
26	Accurate determination of strains at layered materials by selected area electron diffraction mapping. <i>Japanese Journal of Applied Physics</i> , 2019, 58, S11A03.	1.5	1
27	Current-injection quantum-entangled-pair emitter using droplet epitaxial quantum dots on GaAs(111)A. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	11
28	Double-Sided Nonalloyed Ohmic Contacts to Si-doped GaAs for Plasmo-electronic Devices. <i>ACS Omega</i> , 2019, 4, 7300-7307.	3.5	8
29	Transport of a persistent spin helix drifting transverse to the spin texture. <i>Physical Review B</i> , 2019, 99, .	3.2	11
30	Transmission and reflection of charge-density wave packets in a quantum Hall edge controlled by a metal gate. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	3
31	Nonlinear optical response of embedded-semiconductor quantum dots covered by plasmonic metasurfaces. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	2.3	2
32	Field control of anisotropic spin transport and spin helix dynamics in a modulation-doped GaAs quantum well. <i>Physical Review B</i> , 2018, 97, .	3.2	17
33	Superlinear Photoluminescence Dynamics in Plasmon-Quantum-Dot Coupling Systems. <i>ACS Photonics</i> , 2018, 5, 897-906.	6.6	6
34	Strain Relaxation in GaSb/GaAs(111)A Heteroepitaxy Using Thin InAs Interlayers. <i>ACS Omega</i> , 2018, 3, 15592-15597.	3.5	4
35	Evidence for a correlated phase of skyrmions observed in real space. <i>Physical Review B</i> , 2018, 98, .	3.2	1
36	Self-assembled Semiconductor Quantum Ring Complexes by Droplet Epitaxy: Growth and Physical Properties. <i>Nanoscience and Technology</i> , 2018, , 187-228.	1.5	1

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37	Electrically tunable dynamic nuclear spin polarization in GaAs quantum dots at zero magnetic field. Applied Physics Letters, 2018, 112, 142103.	3.3	1
38	Dynamical properties and charge accumulation in solar cells with embedded GaSb quantum dots. Japanese Journal of Applied Physics, 2018, 57, 08RF10.	1.5	1
39	Carrier Transfer in Closely Stacked GaAs/AlGaAs Quantum Dots Grown by Using Droplet Epitaxy. Journal of the Korean Physical Society, 2018, 72, 1356-1363.	0.7	0
40	Optically Imaged Striped Domains of Nonequilibrium Electronic and Nuclear Spins in a Fractional Quantum Hall Liquid. Physical Review Letters, 2017, 118, 076802.	7.8	13
41	Effect of off-cut angle of hydrogen-terminated diamond(111) substrate on the quality of AlN towards high-density AlN/diamond(111) interface hole channel. Journal of Applied Physics, 2017, 121, .	2.5	16
42	Self-assembly of vertically aligned quantum ring-dot structure by Multiple Droplet Epitaxy. Journal of Crystal Growth, 2017, 477, 239-242.	1.5	19
43	Scroll-like Alloyed CdS _x Se _{1-x} Nanoplatelets: Facile Synthesis and Detailed Analysis of Tunable Optical Properties. Chemistry of Materials, 2017, 29, 579-586.	6.7	49
44	Optical transitions in GaNAs quantum wells with variable nitrogen content embedded in AlGaAs. AIP Advances, 2016, 6, .	1.3	3
45	Bias voltage dependence of two-step photocurrent in GaAs/AlGaAs quantum well solar cells. Journal of Applied Physics, 2016, 119, .	2.5	3
46	Type-II recombination dynamics of tensile-strained GaP quantum dots in GaAs grown by droplet epitaxy. Applied Physics Letters, 2016, 109, 171902.	3.3	4
47	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. Applied Physics Express, 2016, 9, 032801.	2.4	19
48	Hyperfine coupling of hole and nuclear spins in symmetric (111)-grown GaAs quantum dots. Physical Review B, 2016, 94, .	3.2	11
49	Growth of Metamorphic InGaAs on GaAs (111)A: Counteracting Lattice Mismatch by Inserting a Thin InAs Interlayer. Crystal Growth and Design, 2016, 16, 5412-5417.	3.0	15
50	Magneto spectroscopy of excited states in charge-tunable GaAs/AlGaAs [111] quantum dots. Physical Review B, 2016, 93, .	3.2	10
51	Hyperfine-controlled domain-wall motion observed in real space and time. Physical Review B, 2016, 94, .	3.2	4
52	Wavelength extension beyond 1.5 μm in symmetric InAs quantum dots grown on InP(111)A using droplet epitaxy. Applied Physics Express, 2016, 9, 101201.	2.4	10
53	Nonlocal biphoton generation in a Werner state from a single semiconductor quantum dot. Physical Review B, 2015, 91, .	3.2	3
54	Precise shape engineering of epitaxial quantum dots by growth kinetics. Physical Review B, 2015, 92, .	3.2	34

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55	Size-dependent line broadening in the emission spectra of single GaAs quantum dots: Impact of surface charge on spectral diffusion. <i>Physical Review B</i> , 2015, 92, .	3.2	33
56	Growth and optical properties of GaSb/GaAs type-II quantum dots with and without wetting layer. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DH01.	1.5	10
57	Extremely High- and Low-Density of Ga Droplets on GaAs{111}A,B: Surface-Polarity Dependence. <i>Crystal Growth and Design</i> , 2015, 15, 485-488.	3.0	18
58	Direct visualization of the N impurity state in dilute GaNAs using scanning tunneling microscopy. <i>Nanoscale</i> , 2015, 7, 16773-16780.	5.6	13
59	Droplet epitaxy growth of telecom InAs quantum dots on metamorphic InAlAs/GaAs(111)A. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DH07.	1.5	13
60	Voltage dependence of two-step photocurrent generation in quantum dot intermediate band solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2015, 134, 108-113.	6.2	23
61	Recent developments in droplet epitaxy. , 2014, , .		0
62	Self-assembly of triangular quantum dots on (111)A substrates by droplet epitaxy. , 2014, , .		1
63	Nitrogen-concentration control in GaNAs/AlGaAs quantum wells using nitrogen δ -doping technique. , 2014, , .		0
64	Tight-binding analysis of the electronic states in AlAs with N isoelectronic impurities. <i>Journal of Applied Physics</i> , 2014, 115, 123501.	2.5	2
65	Composition profiling of GaAs/AlGaAs quantum dots grown by droplet epitaxy. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	13
66	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. <i>Physical Review B</i> , 2014, 90, .	3.2	41
67	Growth of GaSb and AlSb quantum dots on high-index GaAs substrates. <i>Applied Physics Express</i> , 2014, 7, 055502.	2.4	8
68	Nuclear magnetization in gallium arsenide quantum dots at zero magnetic field. <i>Nature Communications</i> , 2014, 5, 3268.	12.8	37
69	Emission from a dipole-forbidden energy state in a GaAs quantum-ring induced by dressed photon. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 115, 1-4.	2.3	5
70	GaAs/AlGaAs quantum wells with indirect-gap AlGaAs barriers for solar cell applications. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	3
71	Heteroepitaxy of GaSb on Si(111) and fabrication of HfO ₂ /GaSb metal-oxide-semiconductor capacitors. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	11
72	Droplet epitaxial growth of highly symmetric quantum dots emitting at telecommunication wavelengths on InP(111)A. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	24

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73	Charge tuning in [111] grown GaAs droplet quantum dots. Applied Physics Letters, 2014, 105, 082111.	3.3	12
74	Self-Assembled Growth of Ga Droplets on GaAs(001): Role of Surface Reconstructions. Crystal Growth and Design, 2014, 14, 3110-3115.	3.0	10
75	Self-assembled Semiconductor Quantum Ring Complexes by Droplet Epitaxy: Growth and Physical Properties. Nanoscience and Technology, 2014, , 161-196.	1.5	4
76	Growth of GaSb quantum dots on GaAs (111)A. E-Journal of Surface Science and Nanotechnology, 2014, 12, 304-306.	0.4	0
77	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. Physical Review B, 2013, 88, .	3.2	116
78	Fabrication of InAs nanoscale rings by droplet epitaxy. Journal of Crystal Growth, 2013, 378, 529-531.	1.5	5
79	Magnetic field induced valence band mixing in [111] grown semiconductor quantum dots. Physical Review B, 2013, 87, .	3.2	24
80	Size-dependent contact angle of Ga droplets on GaAs. Journal of Crystal Growth, 2013, 378, 5-7.	1.5	6
81	Self-assembly of Ga droplets attached to GaAs quantum dots. Journal of Crystal Growth, 2013, 378, 53-56.	1.5	3
82	Growth of GaSb quantum dots on GaAs (311)A. Journal of Crystal Growth, 2013, 378, 475-479.	1.5	7
83	Photo-induced current in n-AlGaAs/GaAs heterojunction channels driven by local illumination at the edge regions of Hall bar. Applied Physics Letters, 2013, 102, 252104.	3.3	2
84	Impacts of ambipolar carrier escape on current-voltage characteristics in a type-I quantum-well solar cell. Applied Physics Letters, 2013, 103, 061118.	3.3	7
85	Post-growth annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1505-1508.	0.8	3
86	Visible single-photon emission from a nitrogen impurity center in AlAs. Applied Physics Letters, 2013, 102, .	3.3	10
87	Emission from a Dipole-Forbidden Energy State in a GaAs Quantum-Ring Induced by Dressed Photon. , 2013, , .		0
88	Extremely high-density GaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2012, 100, .	3.3	33
89	Bunched photon statistics of the spectrally diffusive photoluminescence of single self-assembled GaAs quantum dots. Physical Review B, 2012, 86, .	3.2	19
90	Two-Color Photoexcitation in a GaNAs/AlGaAs Quantum Well Solar Cell. Japanese Journal of Applied Physics, 2012, 51, 06FF15.	1.5	3

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91	Currentâ€“Voltage Characteristics of GaAs/AlGaAs Coupled Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND08.	1.5	3
92	Extension of Absorption Wavelength in GaAs/AlGaAs Quantum Dots with Underlying Quantum Well for Solar Cell Application. Japanese Journal of Applied Physics, 2012, 51, 10ND14.	1.5	0
93	Effects of Sb/As Interdiffusion on Optical Anisotropy of GaSb Quantum Dots in GaAs Grown by Droplet Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 115201.	1.5	0
94	Self-assembly of InAs ring complexes on InP substrates by droplet epitaxy. Journal of Applied Physics, 2012, 112, 063510.	2.5	14
95	Geometrical impact on the optical polarization of droplet epitaxial quantum dots. Physical Review B, 2012, 86, .	3.2	23
96	Anomalous Capacitanceâ€“Voltage Characteristics of GaAs/AlGaAs Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND07.	1.5	0
97	Self-Limiting Growth of Hexagonal and Triangular Quantum Dots on (111)A. Crystal Growth and Design, 2012, 12, 1411-1415.	3.0	44
98	Electrical Lasing in GaAs Quantum Dots Grown by Droplet Epitaxy. , 2012, , .		1
99	Two-Color Photoexcitation in a GaNAs/AlGaAs Quantum Well Solar Cell. Japanese Journal of Applied Physics, 2012, 51, 06FF15.	1.5	9
100	Anomalous Capacitanceâ€“Voltage Characteristics of GaAs/AlGaAs Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND07.	1.5	3
101	Currentâ€“Voltage Characteristics of GaAs/AlGaAs Coupled Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND08.	1.5	5
102	Extension of Absorption Wavelength in GaAs/AlGaAs Quantum Dots with Underlying Quantum Well for Solar Cell Application. Japanese Journal of Applied Physics, 2012, 51, 10ND14.	1.5	2
103	Effects of Sb/As Interdiffusion on Optical Anisotropy of GaSb Quantum Dots in GaAs Grown by Droplet Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 115201.	1.5	4
104	Nitrogen Concentration Dependence on Two-Step Photocurrent Generation in GaNAs/AlGaAs Solar Cells. , 2012, , .		0
105	Anisotropic Diffusion of In Atoms from an In Droplet and Formation of Elliptically Shaped InAs Quantum Dot Clusters on (100) GaAs. Crystal Growth and Design, 2011, 11, 726-728.	3.0	17
106	Two-Step Formation of Gallium Droplets with High Controllability of Size and Density. Crystal Growth and Design, 2011, 11, 4647-4651.	3.0	13
107	Binding Energy of Exciton Complexes in Self-Assembled GaAs Quantum Dots. , 2011, , .		1
108	Dark-Bright Mixing of Interband Transitions in Symmetric Semiconductor Quantum Dots. Physical Review Letters, 2011, 107, 166604.	7.8	41

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109	GaAs Quantum Dots with Type-II Band Alignment. AIP Conference Proceedings, 2011, , .	0.4	0
110	Effects of thermal annealing on C-V characteristics of GaAs δ -AlAs Schottky diodes with embedded Al particles. , 2011, , .		0
111	Carrier and nuclear spin pumping in strain free GaAs/AlGaAs quantum dots grown by droplet epitaxy. , 2011, , .		1
112	Effects of low-temperature capping on the optical properties of GaAs/AlGaAs quantum wells. Nanoscale Research Letters, 2011, 6, 76.	5.7	8
113	Self-Assembled GaAs quantum dots coupled with GaAs wetting layer grown on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 257-259.	0.8	8
114	Growth of GaSb and InSb quantum dots on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 275-277.	0.8	4
115	Photocurrent characteristics in p-n diodes with built-in coupled or uncoupled multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 349-351.	0.8	7
116	Lasing in ultra-narrow emission from GaAs quantum dots coupled with a two-dimensional layer. Nanotechnology, 2011, 22, 335201.	2.6	13
117	Optical anisotropy of GaSb type-II nanorods on vicinal (111)B GaAs. Applied Physics Letters, 2011, 99, 231901.	3.3	5
118	Scanning Fabry-Pérot interferometer with largely tuneable free spectral range for high resolution spectroscopy of single quantum dots. Review of Scientific Instruments, 2011, 82, 073103.	1.3	7
119	Structural atomic-scale analysis of GaAs/AlGaAs quantum wires and quantum dots grown by droplet epitaxy on a (311)A substrate. Applied Physics Letters, 2011, 98, 193112.	3.3	14
120	Shape control of quantum dots studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2011, 109, 102413.	2.5	13
121	Fabrication of GaNAs/AlGaAs Heterostructures with Large Band Offset Using Periodic Growth Interruption. Applied Physics Express, 2011, 4, 125001.	2.4	12
122	Self-Assembly of GaAs Quantum Wires Grown on (311)A Substrates by Droplet Epitaxy. Applied Physics Express, 2011, 4, 055501.	2.4	6
123	Droplet Epitaxy Quantum Ring Structures. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 34-50.	0.5	11
124	Shape Control of QDs Studied by Cross-sectional Scanning Tunneling Microscopy. Journal of the Korean Physical Society, 2011, 58, 1244-1250.	0.7	1
125	Diamagnetic coefficient of excitonic complexes in GaAs/Al _{0.3} Ga _{0.7} As quantum dots. Journal of Physics: Conference Series, 2010, 210, 012012.	0.4	0
126	Fine structure splitting reduction in droplet epitaxy GaAs quantum dots grown on (111)A surface. Journal of Physics: Conference Series, 2010, 245, 012049.	0.4	7

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127	Self-Assembly of Symmetric GaAs Quantum Dots on (111)A Substrates: Suppression of Fine-Structure Splitting. Applied Physics Express, 2010, 3, 065203.	2.4	77
128	Magneto-optical properties of excitonic complexes in GaAs self-assembled quantum dots. Physical Review B, 2010, 81, .	3.2	23
129	Distribution of exciton emission linewidth observed for GaAs quantum dots grown by droplet epitaxy. Journal of Luminescence, 2010, 130, 2390-2393.	3.1	9
130	Poissonian excitonic population of single QDs. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 884-886.	2.7	1
131	Fine structure splitting of quantum dot excitons: Role of geometry and environment. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 881-883.	2.7	10
132	Thermal annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2742-2744.	2.7	2
133	Unstrained GaAs Quantum Dots Grown on GaAs(001) Substrates by Droplet Epitaxy. Applied Physics Express, 2010, 3, 045502.	2.4	28
134	Morphological control of GaAs quantum dots grown by droplet epitaxy using a thin AlGaAs capping layer. Journal of Applied Physics, 2010, 108, 083505.	2.5	14
135	EFFECTS OF ANTIMONY FLUX ON MORPHOLOGY AND PHOTOLUMINESCENCE SPECTRA OF GaSb QUANTUM DOTS FORMED ON GaAs BY DROPLET EPITAXY. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 819-826.	1.8	6
136	FABRICATION OF A GaAs/AlGaAs LATTICE-MATCHED QUANTUM DOT SOLAR CELL. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 681-686.	1.8	7
137	Energy renormalization of exciton complexes in GaAs quantum dots. Physical Review B, 2010, 82, .	3.2	34
138	Atomic scale analysis of self assembled GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2010, 96, .	3.3	60
139	Formation of highly anisotropic GaAs quantum dots on GaAs(001) substrates. Journal of Physics: Conference Series, 2010, 245, 012075.	0.4	0
140	Impact of heavy hole-light hole coupling on optical selection rules in GaAs quantum dots. Applied Physics Letters, 2010, 97, .	3.3	70
141	Optical properties of GaSb/GaAs type- Γ quantum dots grown by droplet epitaxy. Applied Physics Letters, 2009, 94, 081911.	3.3	37
142	Bunching visibility for correlated photons from single GaAs quantum dots. Physical Review B, 2009, 79, .	3.2	25
143	Optical orientation of electron and nuclear spins in strain free GaAs quantum dots grown by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 762-765.	1.5	0
144	Ordering of GaAs quantum dots by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 729-732.	1.5	9

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145	Growth of GaSb dots on GaAs(100) by droplet epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 733-735.	1.5	16
146	Magneto photoluminescence in droplet epitaxial GaAs quantum rings. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 861-863.	1.5	7
147	Quantum dots to double concentric quantum ring structures transition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 928-931.	0.8	4
148	Line broadening of excitonic complexes in self-assembled GaAs/AlGaAs single quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 886-889.	0.8	2
149	High resolution spectroscopy of self-assembled single GaAs/AlGaAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 890-893.	0.8	1
150	Advanced quantum dot and photonic crystal technologies for integrated nanophotonic circuits. <i>Microelectronics Journal</i> , 2009, 40, 736-740.	2.0	5
151	High-density GaAs/AlGaAs quantum dots formed on GaAs (311)A substrates by droplet epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 1828-1831.	1.5	24
152	Spontaneous formation of a cluster of InAs dots along a ring-like zone on GaAs (100) by droplet epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 1836-1838.	1.5	5
153	Two different growth modes of GaSb dots on GaAs(100) by droplet epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 2255-2257.	1.5	11
154	Photon antibunching in double quantum ring structures. <i>Physical Review B</i> , 2009, 79, .	3.2	44
155	Self-assembly of quantum dots and rings by droplet epitaxy and their optical properties. <i>Journal of Nanophotonics</i> , 2009, 3, 031605.	1.0	23
156	Self-assembly of quantum dots and rings by droplet epitaxy and their optical properties. <i>Chinese Optics Letters</i> , 2009, 7, 879.	2.9	1
157	Electronic structure of GaAs/AlGaAs quantum double rings in lateral electric field. <i>Chinese Optics Letters</i> , 2009, 7, 882-885.	2.9	2
158	Ultra-narrow emission from single GaAs self-assembled quantum dots grown by droplet epitaxy. <i>Nanotechnology</i> , 2009, 20, 395601.	2.6	65
159	Poissonian statistics of excitonic complexes in quantum dots. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	42
160	Structural properties of GaAs nanostructures formed by a supply of intense As ₄ flux in droplet epitaxy. <i>Applied Surface Science</i> , 2008, 254, 7770-7773.	6.1	18
161	Anomalous temperature dependence of the carrier capture time into InAs/GaAs quantum dots grown on a quantum wire array. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1879-1881.	2.7	1
162	Magneto-photoluminescence study in single GaAs/AlGaAs self-assembled quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1982-1984.	2.7	2

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163	Fabrication of a complex InAs ring-and-dot structure by droplet epitaxy. Applied Surface Science, 2008, 254, 7777-7780.	6.1	19
164	Optically monitored nuclear spin dynamics in individual GaAs quantum dots grown by droplet epitaxy. Physical Review B, 2008, 78, .	3.2	38
165	Rapid thermal annealing effects on self-assembled quantum dot and quantum ring structures. Journal of Applied Physics, 2008, 104, .	2.5	40
166	Exciton fine structure in strain-free GaAs quantum dots: Extrinsic effects. Physical Review B, 2008, 78, .	3.1	24
167	Spectral diffusion and line broadening in single self-assembled $\text{GaAs}/\text{AlGaAs}$ quantum dot photoluminescence. Applied Physics Letters, 2008, 93, .	3.3	62
168	Carrier dynamics in individual concentric quantum rings: Photoluminescence measurements. Physical Review B, 2008, 77, .	3.2	32
169	Acceleration and suppression of photoemission of GaAs quantum dots embedded in photonic crystal microcavities. Applied Physics Letters, 2008, 93, 111103.	3.3	18
170	$\text{GaAs}/\text{AlGaAs}$ quantum dot laser fabricated on GaAs (311)A substrate by droplet epitaxy. Applied Physics Letters, 2008, 93, 203110.	3.3	35
171	Phonon sideband recombination kinetics in single quantum dots. Journal of Applied Physics, 2008, 104, .	2.5	10
172	Structure of Nanowires Fabricated by Electron Beam Induced Deposition to Connect Self-Assembled Quantum Structures. Japanese Journal of Applied Physics, 2007, 46, 6277-6281.	1.5	4
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